



Product Change Notice

Micron PCN: 30939
Date: 7/17/2013

Type of Change:	Manufacturing Site Change	
Title of Change:	50nm 1Gb DDR2 (U68A) Fab Site Transition (from Singapore to Virginia, USA)	
Description of Change:	Fabrication of Micron's 1Gb 50 nm DDR2 (U68A) parts will move from Singapore (Fab 7) to Virginia, USA (Fab 6). Transition out of the Fab in Singapore will be complete by January, 2014.	
Reason for Change:	Optimization of Manufacturing Efficiency	
Contact Information:	<u>Marketing Contact</u> Sven Evers SEVERSM@MICRON.COM Micron Semiconductor Prds	<u>Engineering Contact</u> Denzil Rogers DENZILROGERS@MICRON.COM Micron Semiconductors Prds

Product Affected: All 50nm 1Gb DDR2 (U68A) Parts

Affected Micron Part Numbers

MT47H128M8CF-25E AIT:H	MT47H128M8CF-3 IT:H	MT47H64M16HR-3 AAT:H
MT47H128M8CF-25E IT:H	MT47H64M16HR-25 IT:H	MT47H64M16HR-3 AIT:H
MT47H128M8CF-3 AAT:H	MT47H64M16HR-25E AAT:H	MT47H64M16HR-3 IT:H
MT47H128M8CF-3 AIT:H	MT47H64M16HR-25E AIT:H	MT47H64M16HR-3:H
MT47H64M16HR-25:H	MT47H64M16HR-25E IT:H	

Method of Identification:

Component Mark: The first character in the "country of diffusion-encapsulation" code in the component mark for product fabricated will change from "2" (Singapore) to "1" (USA). Please refer to Micron Customer Service Note-11 for detailed description of marking codes (<http://download.micron.com/pdf/csnotes/csn11.pdf>)

Micron Sites Affected:	Micron Manassas (MTV), Micron Singapore (Tech)
Qual Data Available:	1-Aug-2013
Sample Available:	15-Aug-2013
Product Ship Date:	1-Oct-2013
